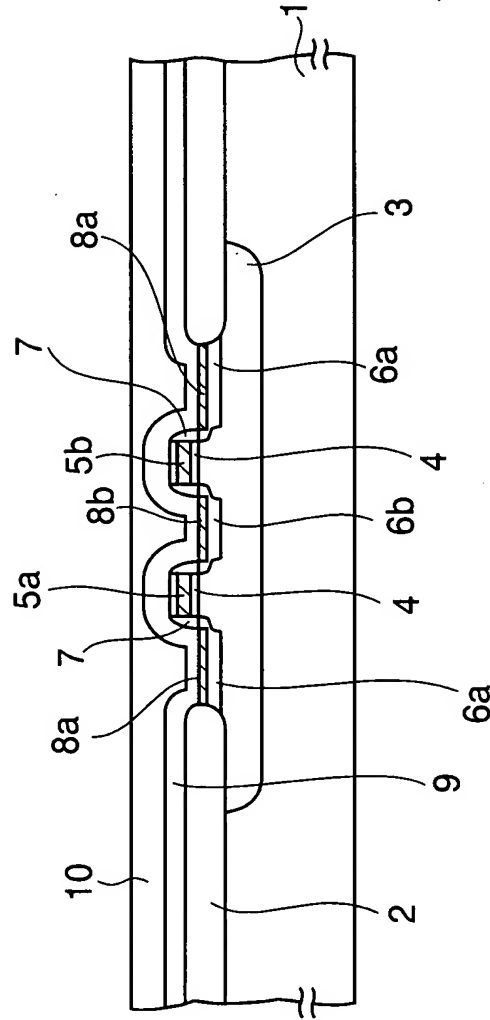


FIG. 1A



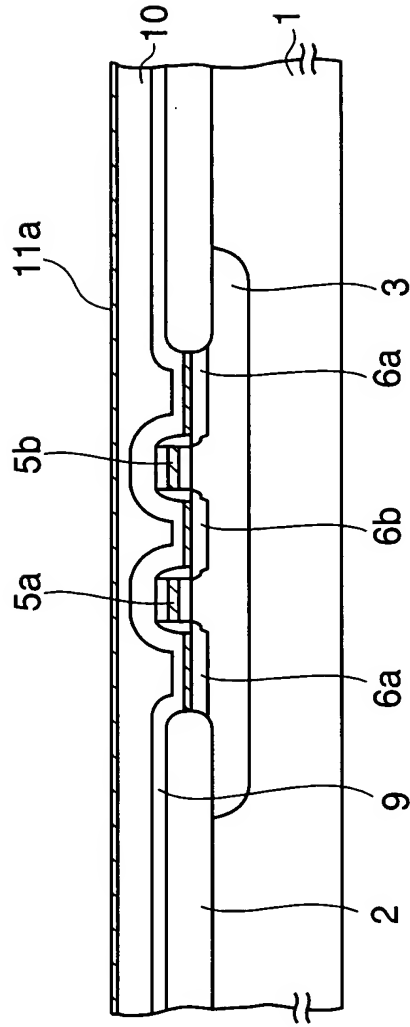


FIG. 1B

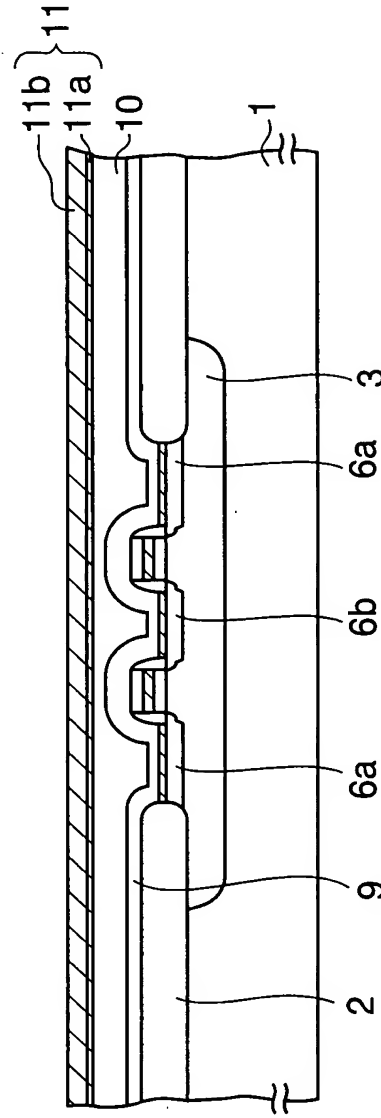


FIG. 1C

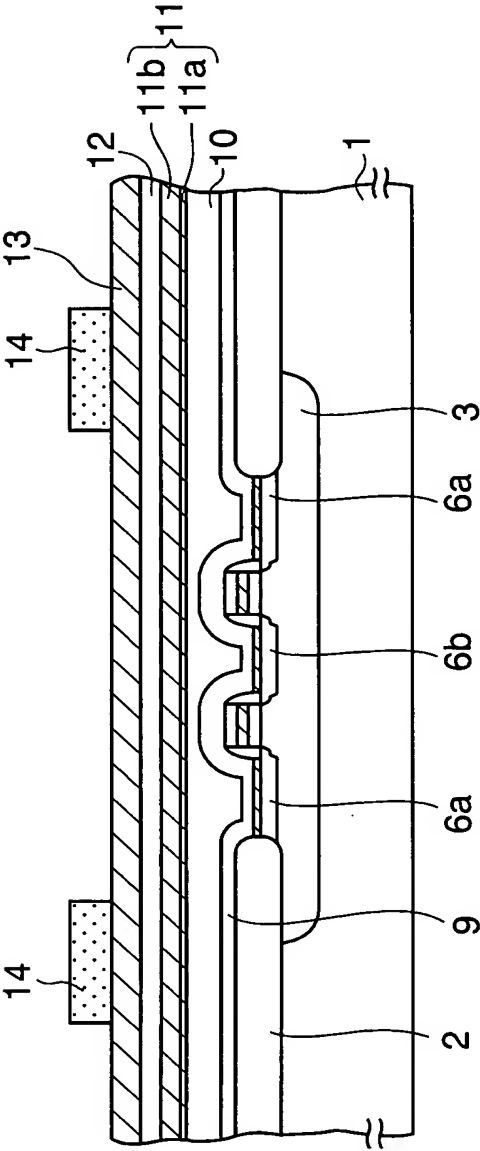


FIG. 1D

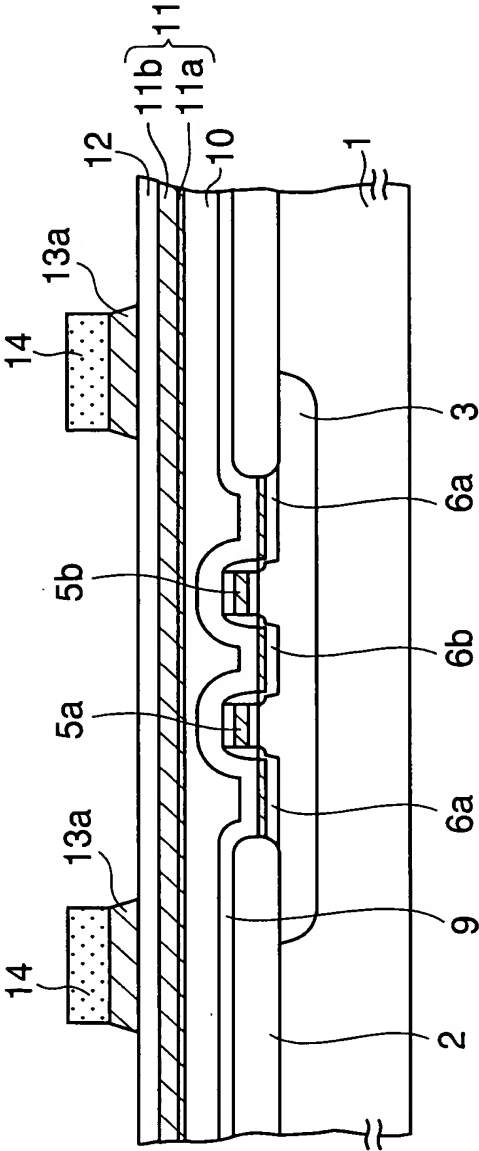


FIG. 1E

[illegible]

FIG. 1G

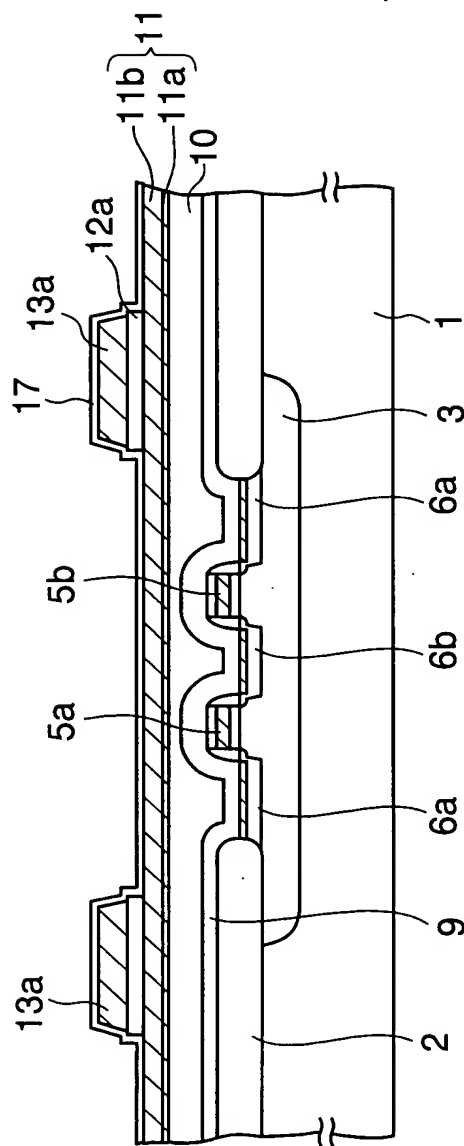


FIG. 1H

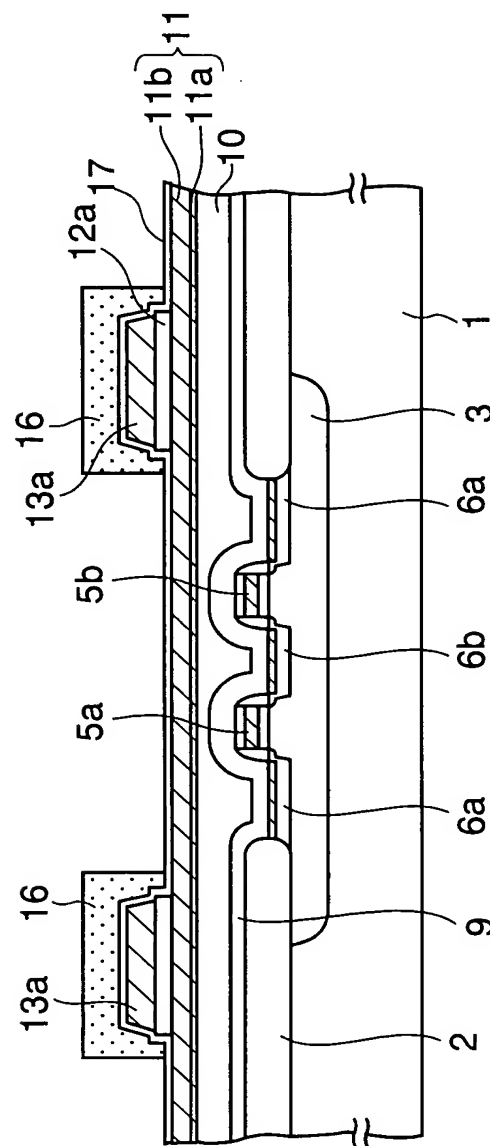


FIG. 1I

This cross-sectional view shows a semiconductor device with a central channel region (10) and side contact regions (11a, 11b, 11c). The channel region is defined by a central layer (10) and is flanked by side contact regions (11a, 11b, 11c). The side contact regions are formed by a stack of layers (11a, 11b, 11c) and are connected to a common contact pad (12a). The device is mounted on a substrate (1) and includes a central contact pad (12a) and side contact pads (12b, 12c). The central contact pad (12a) is connected to a common contact pad (12a) and the side contact pads (12b, 12c) are connected to a common contact pad (12a).

FIG. 1K

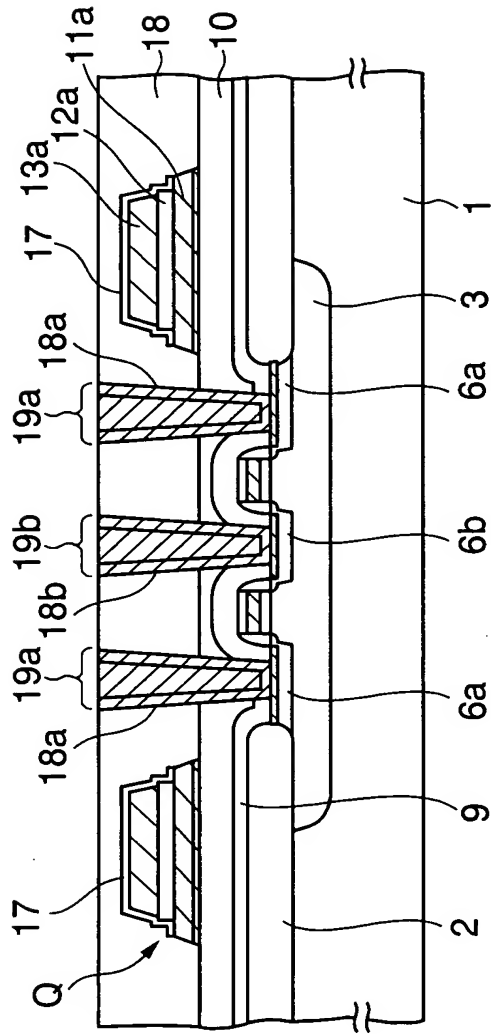


FIG. 11L

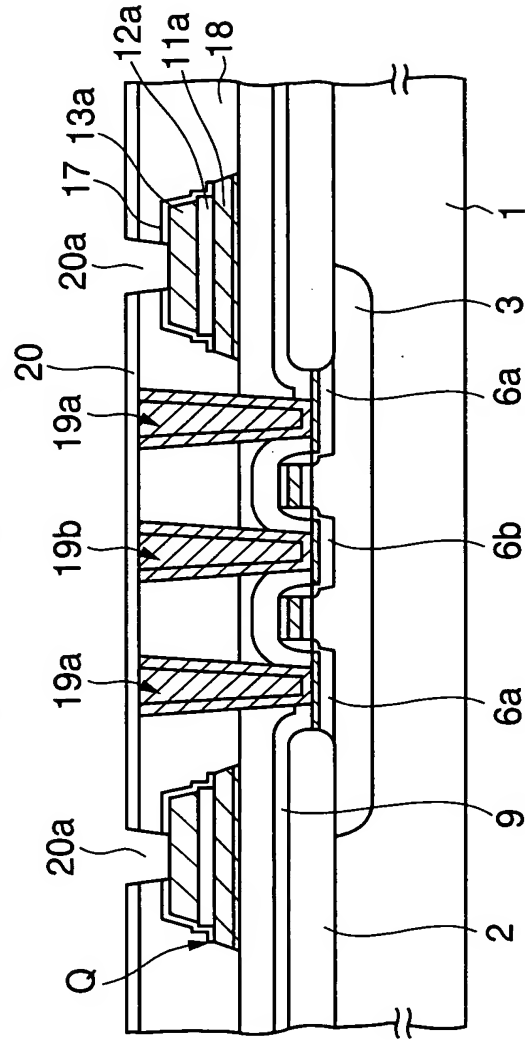


FIG. 1M

FIG. 1N

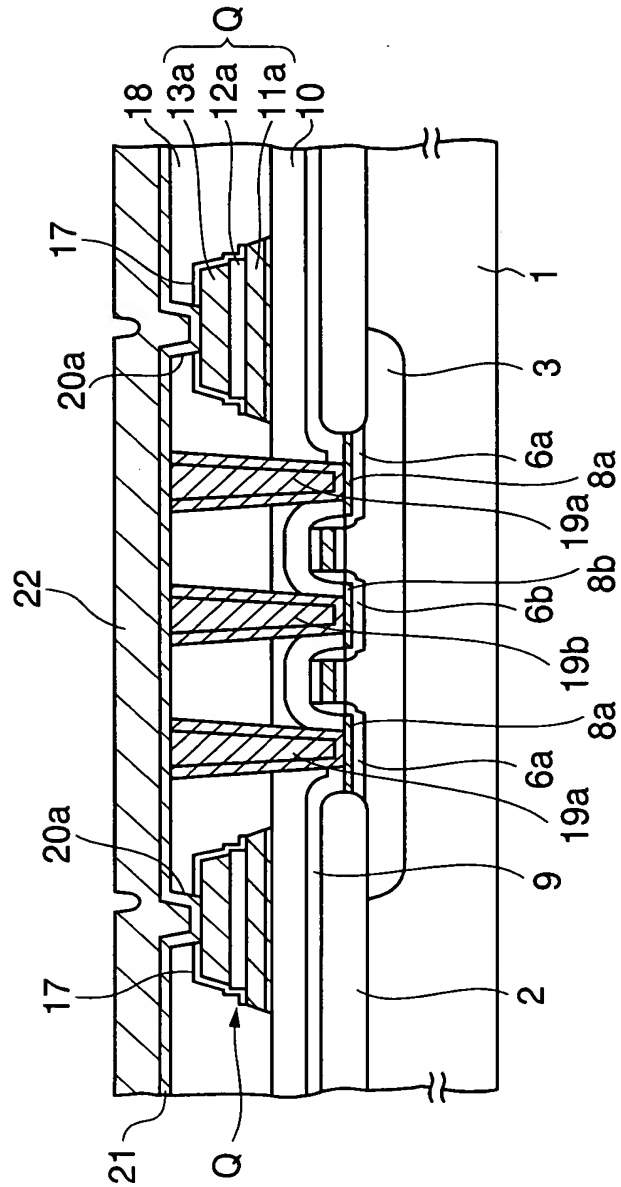


FIG. 10

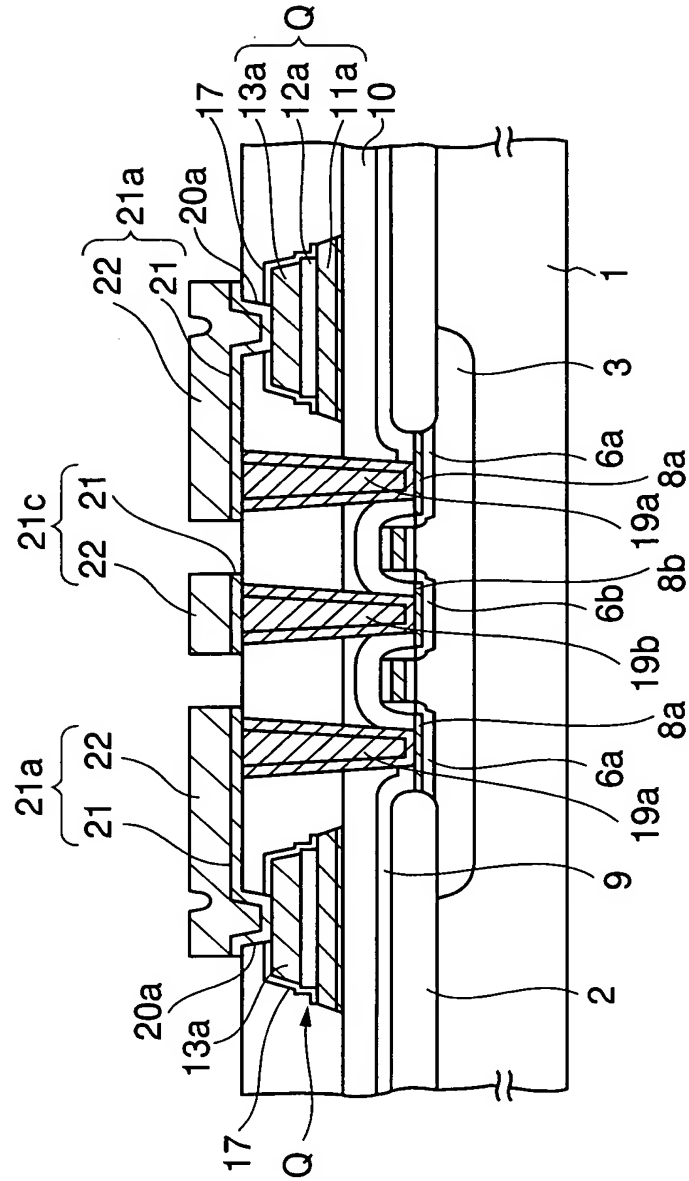


FIG. 1P

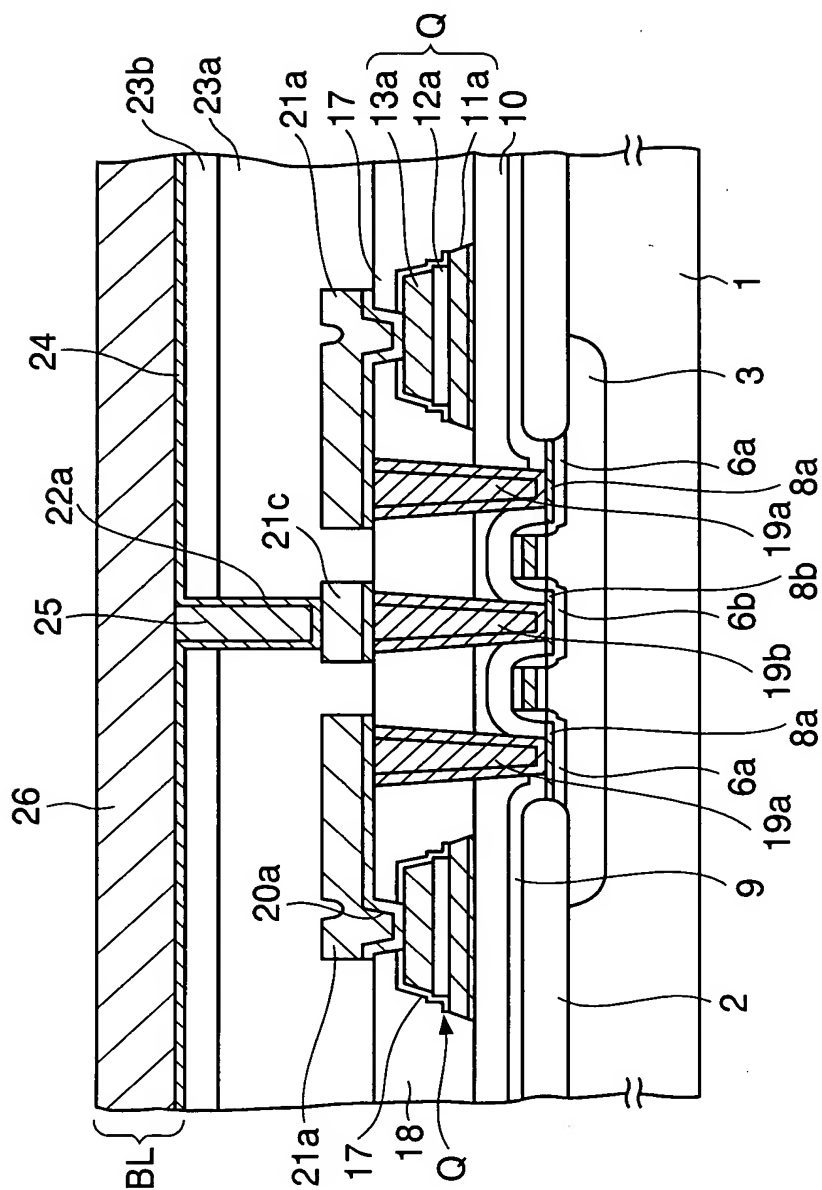


FIG. 2

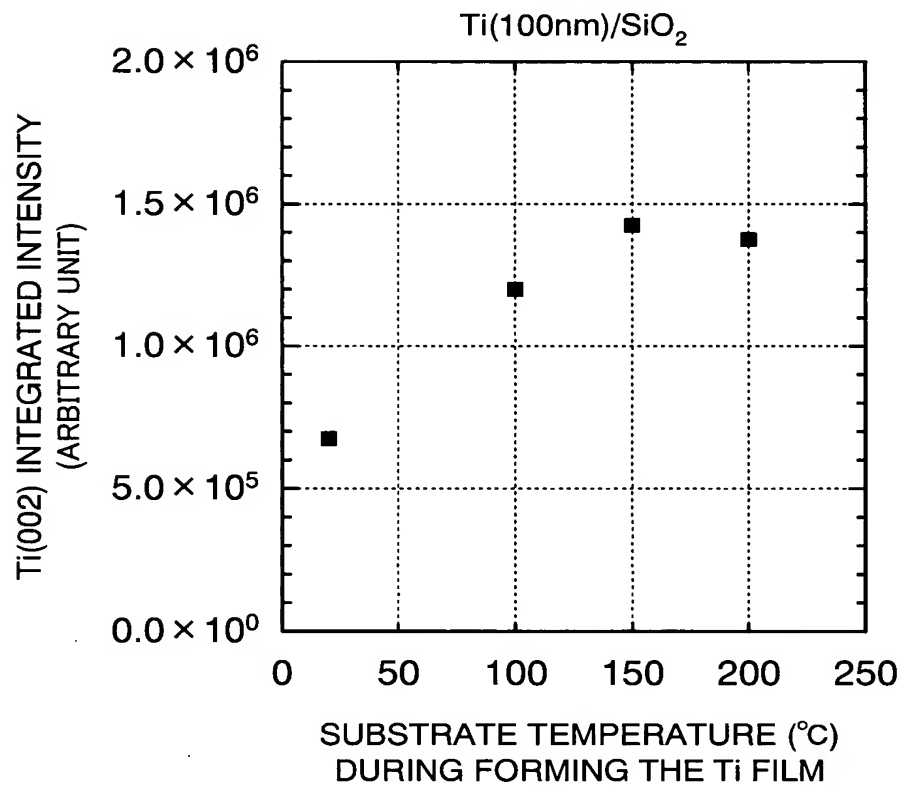


FIG. 3

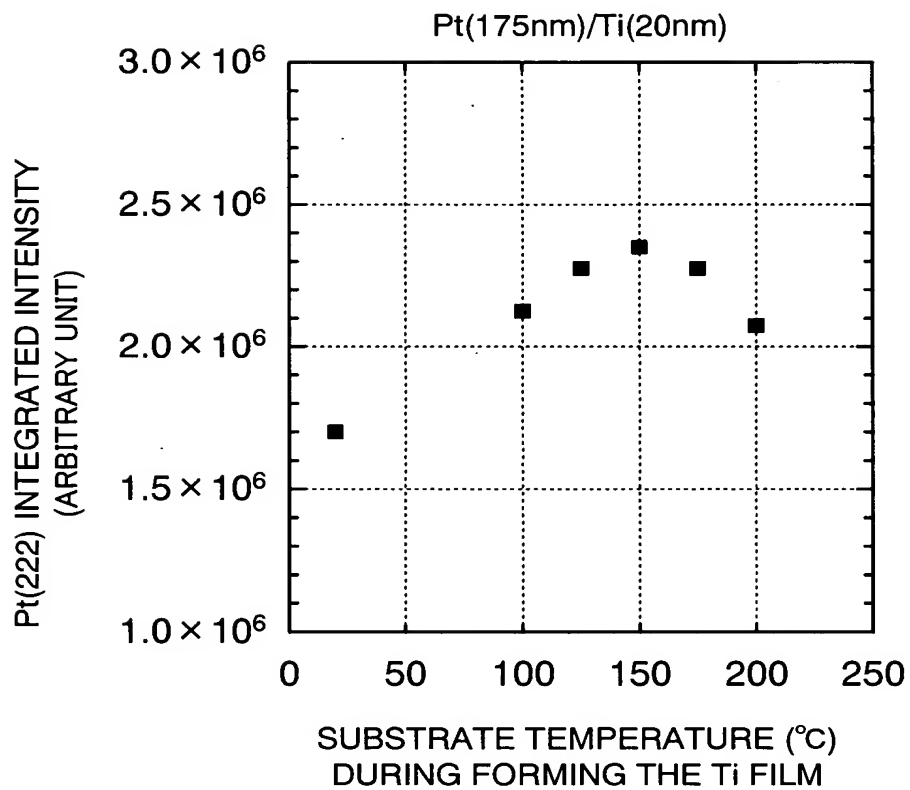


FIG. 4

